

# isc N-Channel Mosfet Transistor

## **IRF540**

### FEATURES

- Low R<sub>DS(on)</sub>
- V<sub>GS</sub> Rated at ±20V
- Silicon Gate for Fast Switching Speed
- Rugged
- Low Drive Requirements
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### APPLICATIONS

• Designed especially for high voltage, high speed applications, such as off-line switching power supplies, UPS, AC and DC motor controls, relay and solenoid drivers.

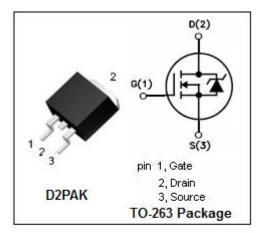


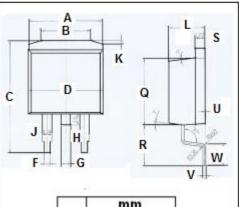
(ia <b>10</b> )						
SYMBOL	PARAMETER	VALUE	UNIT			
V <sub>DSS</sub>	Drain-Source Voltage	100	V			
V <sub>GS</sub>	Gate-Source Voltage-Continuous	±20	V			
lo	Drain Current-Continuous@ TC=25°C	28	- A			
	Drain Current-continuous@ TC=100°C	20				
I <sub>DM</sub>	Drain Current-Single Plused	110	А			
PD	Total Dissipation @Tc=25°C	100	W			
Tj	Max. Operating Junction Temperature		°C			
T <sub>stg</sub>	Storage Temperature	-55~175	°C			



SYMBOL	PARAMETER	МАХ	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.5	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	62	°C/W

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	mm	
DIM	MIN	MAX
A		0
В	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
Н	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
0	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
٧	0.37	0.39
W	2.80	2.82



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#### **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA	100			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 0.25mA	2		4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 17A			0.077	Ω
lgss	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 100V; V <sub>GS</sub> =0			25	uA
Vsd	Forward On-Voltage	I <sub>S</sub> = 28A; V <sub>GS</sub> =0			2.5	V

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